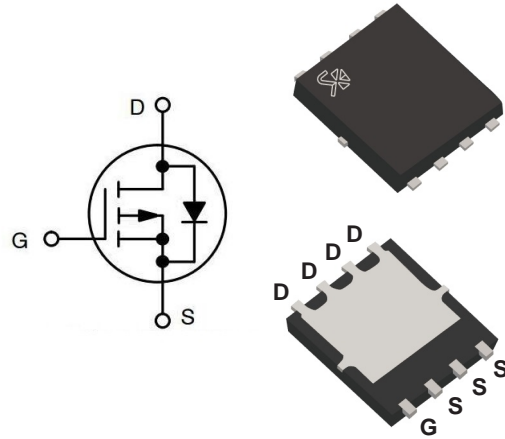


Feature

- 20V P-Channel MOSFET High Dense Design.
- Ultra low On-Resistance.
- $R_{DS(ON)} = 6m\Omega$ (typ.) @ $V_{GS} = -4.5V$
- $R_{DS(ON)} = 7.5m\Omega$ (typ.) @ $V_{GS} = -2.5V$
- Reliable and Rugged.



Applications

- Power Management in Notebook Computer, and Portable Equipment and Battery Systems.

PDFN5060

Electrical Characteristics

1. Absolute Maximum Ratings ($T_A = 25^\circ C$ Unless Otherwise Noted)

Symbol	Parameter	Rating	Unit
V_{DSS}	Drain-Source Voltage	-20	V
V_{GSS}	Gate-Source Voltage	± 12	
I_D	Continue Drain Current	-40	A
I_{DM}	Pulsed Drain Current	-160	
I_S	Diode Continuous Forward Current	-40	A
T_J	Maximum Junction Temperature	150	$^\circ C$
T_{STG}	Storage Temperature Range	-55 to 150	

2. Static Electrical Characteristics ($T_A = 25^\circ C$ Unless Otherwise Noted)

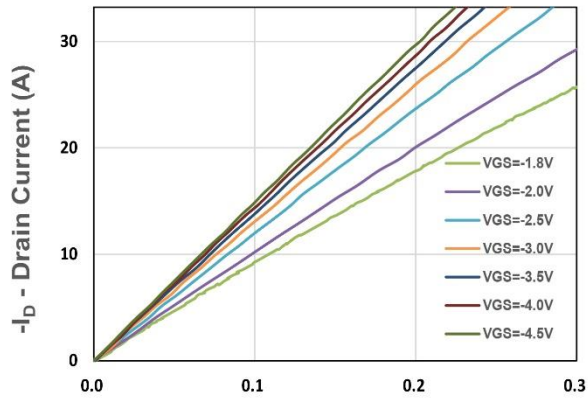
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=-250\mu A$	-20			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-16V, V_{GS}=0V$ $T_J=85^\circ C$			-1 -30	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.4	-0.6	-0.8	V
I_{GSS}	Gate Body Leakage Current	$V_{GS}=\pm 12V, V_{DS}=0V$			± 100	nA
$R_{DS(ON)}$	Drain-Source On-state Resistance	$V_{GS}=-4.5V, I_{DS}=-2A$ $V_{GS}=-2.5V, I_{DS}=-2A$		6 7.5	8 9	$m\Omega$
V_{SD}	Diode Forward Voltage	$I_{SD}=-2A, V_{GS}=0V$		-0.6	-1.3	V

*Note:

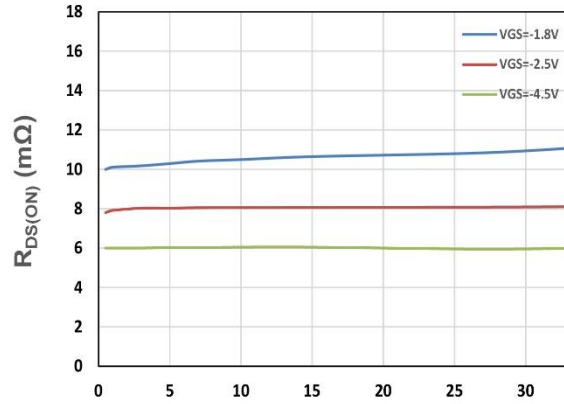
a : Current maybe limit by bonding wire.

b : The $R_{\theta JA}$ is the sum of the thermal impedance from junction to ambient and depend on package type.

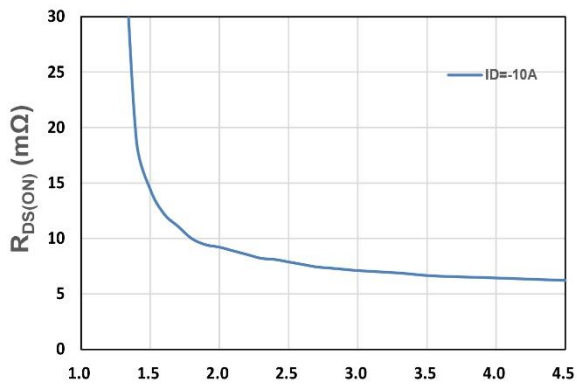
TYPICAL CHARACTERISTICS



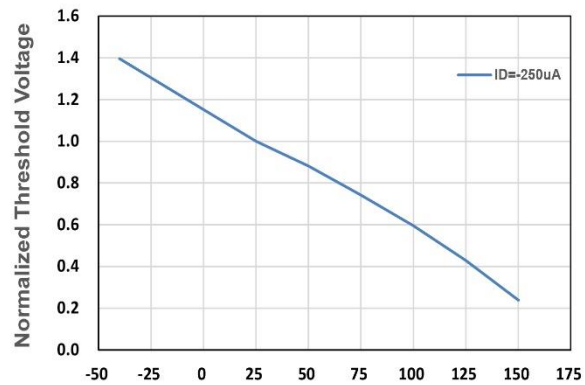
- V_{DS} - Drain - Source Voltage (V)
Figure 1. Output Characteristics



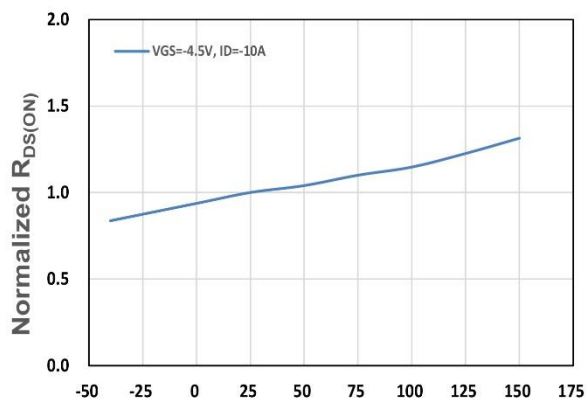
- I_D - Drain Current (A)
Figure 2. On-Resistance vs. ID



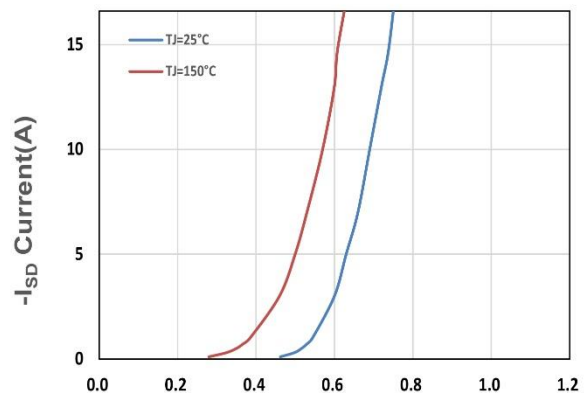
- V_{GS} - Gate - Source Voltage (V)
Figure 3. On-Resistance vs. VGS



T_j , Junction Temperature(°C)
Figure 4. Gate Threshold Voltage



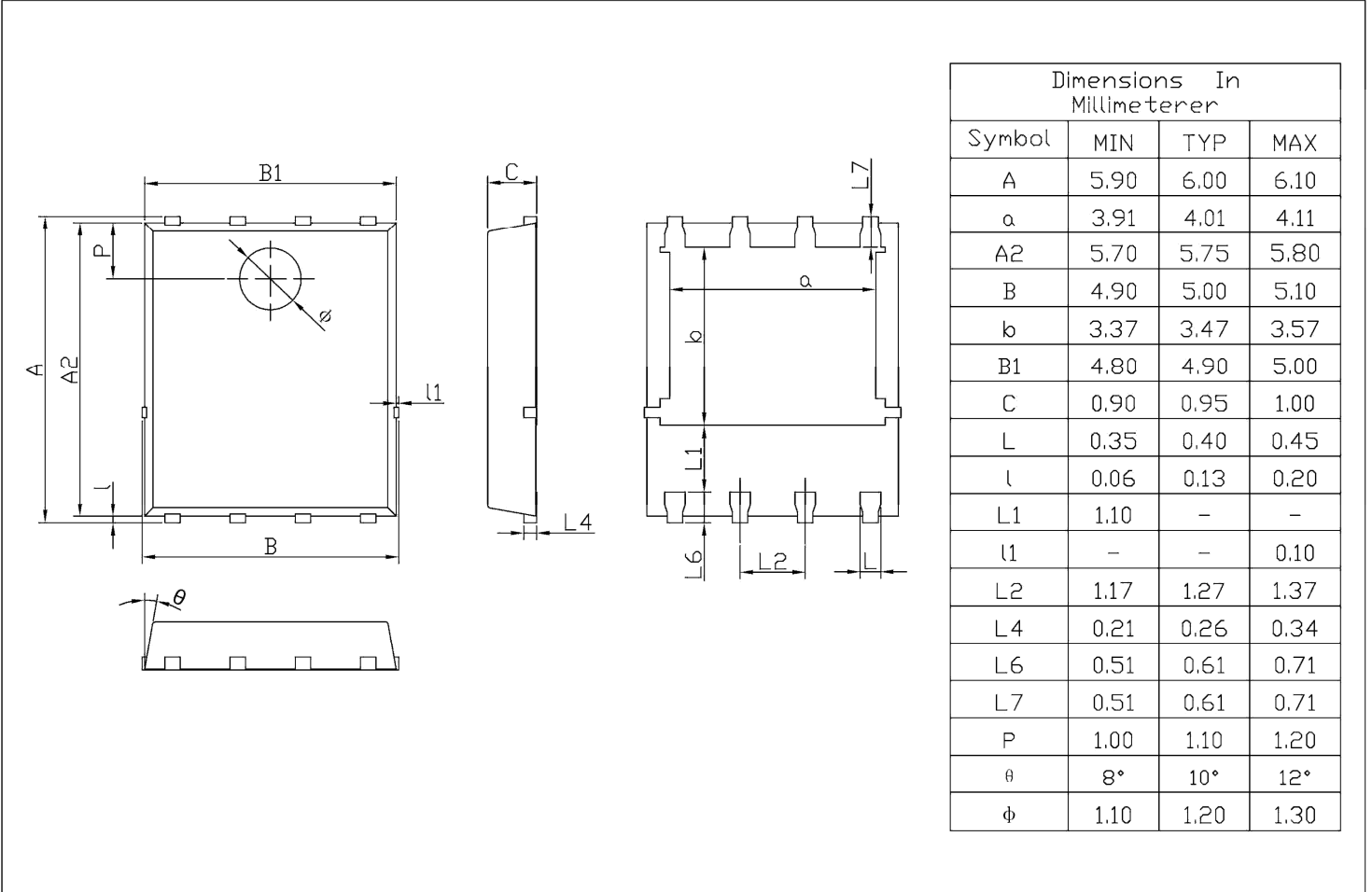
T_j , Junction Temperature(°C)
Figure 5. Drain-Source On Resistance



- V_{SD} , Source-Drain Voltage(V)
Figure 6. Source-Drain Diode Forward

PDFN5060

Unit:mm



单击下面可查看定价，库存，交付和生命周期等信息

[>>SHIKUES\(时科\)](#)